

TSMC 98-262  
Serial Number 09/325,951



**PRELIMINARY AMENDMENT**

#9/c  
9/27/01  
V. Vannale  
SEP 26 2001  
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**TO:** COMMISSIONER OF PATENTS AND TRADEMARKS  
Washington, D. C. 20231

**FROM:** George O. Saile ( Reg. No. 19,572)  
20 McIntosh Drive  
Poughkeepsie, NY 12603

**DATE:** 17 September 2001

**REF:** APPLICANT : Chiang et al.  
SERIAL NO. : 09/325,951  
ART UNIT : 2812  
FILING DATE : 04/06/99  
ATT'Y NO. : TSMC 98-262  
EXAMINER : R. Pompey  
TITLE : Method for Forming High Purity Silicon Oxide Field  
Oxide Isolation Region

Sir:

In response to an advisory action mailed on 07 August 2001, please consider the following amendments and remarks pertaining to the above referenced application.

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class mail in an envelope addressed to the Commissioner of Patents and Trademarks, Washington, D. C. 20231 on 21 September 2001

Stephen B Ackerman  
Name Reg #37,761

JSB  
Signature

9/21/01  
Date